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## What is claimed is:

1. A high-frequency switching module primarily including a switching circuit and a filtering circuit, comprising:

a multi-layer assembly having a plurality of dielectric sheets of layers placed one over the other;

a plurality of high-frequency terminals provided on outer surfaces of the multi-layer assembly;

said switching circuit formed in the layers of said multi-layer assembly, having one end thereof connected to a first high-frequency terminal of said plurality of high-frequency terminals; and

said filtering circuit formed in the layers of said multilayer assembly, having one end thereof connected to the other end of said switching circuit and the other end connected to a second high-frequency terminal of said plurality of high-frequency terminals,

wherein said high-frequency terminals are provided on a mounting side surface of said multi-layer assembly while lateral sides of said multi-layer assembly are not provided with any electrode for said high-frequency terminals.

2. The high-frequency switching module according to claim 1, wherein the connection between one end of the switching circuit and the first high-frequency terminal and

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the connection between the other end of the filtering circuit and the second high-frequency terminal are implemented through corresponding via-holes provided in the multi-layer assembly.

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3. The high-frequency switching module according to claim 1, wherein the multi-layer assembly has a grounding electrode provided on a dielectric sheet closer to the mounting side surface than from the filtering circuit and the switching circuit within the multi-layer assembly and the grounding electrode extends to an outer edge of the dielectric sheet.

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4. The high-frequency switching module according to claim 1, wherein each of the high-frequency terminals is arranged extending along the outer edge of the mounting side surface of the multi-layer assembly so that each electrode width at the outer edge of said multi-layer assembly is greater than that at the inner region of the same.

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5. The high-frequency switching module according to claim 4, wherein the high-frequency terminals are formed of substantially a D character shape.

6. The high-frequency switching module according to claim 4, wherein the high-frequency terminals are positioned as spaced by a given distance from the outer edge of the multi-layer assembly.

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7. The high-frequency switching module according to claim 1, wherein said multi-layer assembly has a rectangular four-sided outer shape and has connection terminals provided at corners of the mounting side surface thereof for external connection reinforcement.

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8. The high-frequency switching module according to claim 1, wherein said multi-layer assembly has a rectangular four-sided outer shape and has connection terminals provided at an inner region of the mounting side surface thereof for external connection reinforcement.

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9. The high-frequency switching module according to claim 8, wherein the connection terminals are positioned at substantially the center of the mounting side surface of the multi-layer assembly.

10. The high-frequency switching module according to claim 9, wherein the connection terminals are positioned in symmetry with respect to substantially the center of the

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mounting side surface of the multi-layer assembly.

- 11. The high-frequency switching module according to claim 8, wherein the connection terminals are connected to the grounding electrodes through corresponding via-holes provided in said multi-layer assembly.
- 12. The high-frequency switching module according to claim 1, wherein the high-frequency terminals are equipped with solder balls.
- 13. The high-frequency switching module according to claim 1, wherein at least one of the high-frequency terminals is located opposite to an inner electrode which forms the one end of the high-frequency switching module comprised of the switching circuit and the filtering circuit, thus forming a capacitor circuit.
  - 14. A high-frequency apparatus comprising:
- a high-frequency switching module defined in claim 1;
  - a circuit board on which the high-frequency switching module is mounted, wherein
  - lands provided on said circuit board are arranged smaller in size than the high-frequency terminals of said

high-frequency switching module.

15. A high-frequency switching module primarily including a switching circuit and a filtering circuit, comprising:

a multi-layer assembly having a plurality of dielectric sheets of layers placed one over the other;

a plurality of high-frequency terminals provided on outer surfaces of the multi-layer assembly;

said switching circuit formed in the layers of said multi-layer assembly, having one end thereof connected to a first high-frequency terminal of said plurality of high-frequency terminals; and.

said filtering circuit formed in the layers of said multilayer assembly, having one end thereof connected to the other end of said switching circuit and the other end connected to a second high-frequency terminal of said plurality of high-frequency terminals,

wherein a multi-layer capacitor which forms a part of said switching circuit and/or the filtering circuit is mounted on said multi-layer assembly so that the direction of stacking layers in said multi-layer assembly extends substantially vertical to the direction of stacking paired capacitor electrodes provided on layers of said multi-layer capacitor.

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16. A high-frequency switching module primarily including a switching circuit and a filtering circuit, comprising:

a multi-layer assembly having a plurality of dielectric sheets of layers placed one over the other;

a plurality of high-frequency terminals provided on outer surfaces of the multi-layer assembly;

said switching circuit formed in the layers of said multi-layer assembly, having one end thereof connected to a first high-frequency terminal of said plurality of high-frequency terminals; and

said filtering circuit formed in the layers of said multilayer assembly, having one end thereof connected to the other end of said switching circuit and the other end connected to a second high-frequency terminal of said plurality of high-frequency terminals,

wherein a chip inductor which forms a part of said switching circuit and/or the filtering circuit is mounted on said multi-layer assembly so that the axis of electrode coils in said chip inductor extends substantially vertical to the axis of a spiral transmission line which forms a part of said switching circuit and/or the filtering circuit in said multi-layer assembly.

17. A high-frequency switching module primarily including a switching circuit and a filtering circuit, comprising:

a multi-layer assembly having a plurality of dielectric sheets of layers placed one over the other;

a plurality of high-frequency terminals provided on outer surfaces of the multi-layer assembly;

said switching circuit formed in the layers of said multi-layer assembly, having one end thereof connected to a first high-frequency terminal of said plurality of high-frequency terminals; and

said filtering circuit formed in the layers of said multilayer assembly, having one end thereof connected to the other end of said switching circuit and the other end connected to a second high-frequency terminal of said plurality of high-frequency terminals,

wherein a strip line which forms a part of said switching circuit and/or the filtering circuit is partially located in said multi-layer assembly while the remaining part of the strip line is located on a circuit board on which said multi-layer assembly is mounted.

18. The high-frequency switching module according to claim 17, wherein the strip line which is connected to a control terminal for controlling the switching circuit is

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19. The high-frequency switching module according to claim 17, wherein the impedance of the strip line located in the multi-layer assembly is smaller than the impedance of the strip line located on the circuit board so that the total electric length is not greater than  $\lambda/4$ .

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